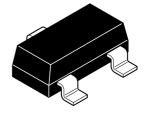


# **ZXTP08400BFF** 400V, SOT23F, PNP medium power high voltage transistor

### Summary;

 $BV_{CEO} > -400V$   $BV_{ECO} > -6V$   $I_{C(cont)} = -0.2A$   $V_{CE(sat)} < 220mV @ 100mA$  $P_D = 1.5W$ 

### Complementary part number ZXTN08400BFF



## Description

This PNP transistor has been designed for applications requiring high blocking voltage. The SOT23F package is pin compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

## Features

- High voltage
- Low saturation voltage

### Applications

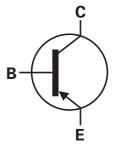
• Telecoms switching

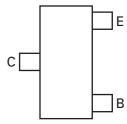
### **Ordering information**

Device	Reel size	Tape width	Quantity	
	(inches)	(mm)	per reel	
ZXTP08400BFFTA	7	8	3000	

### **Device marking**

1D6





Pinout - top view

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	-400	V
Collector-emitter voltage	V <sub>CEO</sub>	-400	V
Emitter-collector voltage (reverse blocking)	V <sub>ECO</sub>	-6	V
Emitter-base voltage	V <sub>EBO</sub>	-7	V
Continuous collector current <sup>(c)</sup>	۱ <sub>C</sub>	-0.2	А
Peak pulse current	I <sub>СМ</sub>	-1	А
Base current	۱ <sub>B</sub>	-0.2	А
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$		0.84	W
Linear derating factor	P <sub>D</sub>	P <sub>D</sub> 6.72	
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$		1.34	W
Linear derating factor	P <sub>D</sub>	10.72	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$		1.50	W
Linear derating factor	P <sub>D</sub>	12.0	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$		2.0	W
Linear derating factor	P <sub>D</sub>	16.0	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

### **Thermal resistamce**

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	149	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	93	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	83	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\Theta JA}$	60	°C/W

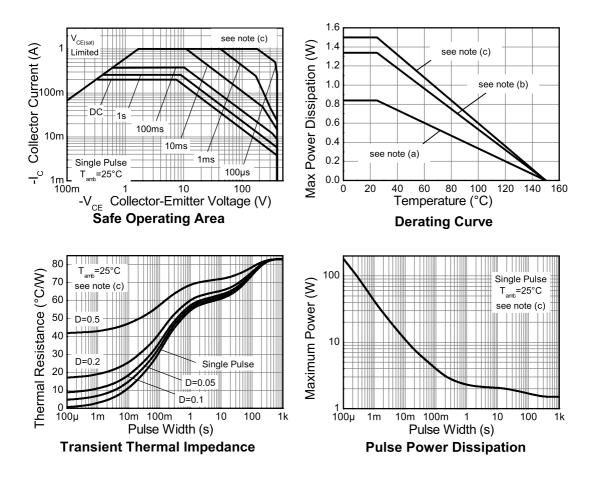
NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on  $25 \text{mm} \times 25 \text{mm} \times 1.6 \text{mm}$  FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (c) Mounted on  $50 \text{mm} \times 50 \text{mm} \times 1.6 \text{mm}$  FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at t<5 secs.

## Characteristics



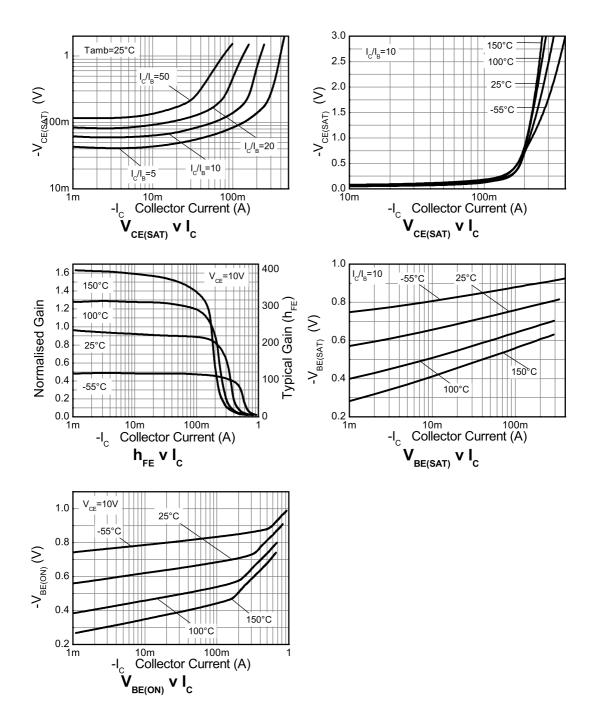
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	-400	-500		V	I <sub>C</sub> = -100μΑ
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	-400	-480		V	I <sub>C</sub> = -10mA <sup>(*)</sup>
Emitter-base breakdown voltage	BV <sub>EBO</sub>	-7	-8.1		V	I <sub>E</sub> = -100μA
Emitter-collector breakdown voltage (reverse blocking)	BV <sub>ECX</sub>	-6	-8.2		V	$\begin{split} I_{\text{E}} &= -100 \mu \text{A}, \ \text{R}_{\text{BC}} < 1 \text{k} \Omega \text{ or} \\ 0.25 \text{V} > \text{V}_{\text{BC}} > -0.25 \text{V} \end{split}$
Emitter-collector breakdown voltage (base open)	BV <sub>ECO</sub>	-6	-8.6		V	I <sub>E</sub> = -100μA,
Collector-base cut-off current	I <sub>CBO</sub>		<-1	-50	nA	V <sub>CB</sub> = -320V
				-20	μA	$V_{CB} = -320V, T_{amb} = 100^{\circ}C$
Emitter-base cut-off current	I <sub>EBO</sub>		<-1	-50	nA	V <sub>EB</sub> = -5.6V
Collector-emitter saturation	V <sub>CE(sat)</sub>		-10	-145	mV	I <sub>C</sub> = -20mA, I <sub>B</sub> = -1mA <sup>(*)</sup>
voltage			-95	-125	mV	l <sub>C</sub> = -50mA, l <sub>B</sub> = -5mA <sup>(*)</sup>
			-140	-220	mV	$I_{C} = -100 \text{mA}, I_{B} = -10 \text{mA}^{(*)}$
			-140	-190	mV	$I_{C} = -200 \text{mA}, I_{B} = -40 \text{mA}^{(*)}$
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		-810	-900	mV	$I_{\rm C}$ = -200mA, $I_{\rm B}$ = -40mA <sup>(*)</sup>
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-705	-800	mV	$I_{C}$ = -200mA, $V_{CE}$ = -10 $V^{(*)}$
Static forward current	h <sub>FE</sub>	100	220			$I_{C} = -1mA, V_{CE} = -5V^{(*)}$
transfer ratio		100	200	300		I <sub>C</sub> = -50mA, V <sub>CE</sub> = -5V <sup>(*)</sup>
		100	200			$I_{C} = -200 \text{mA}, V_{CE} = -10 V^{(*)}$
Transition frequency	f <sub>T</sub>	50	70		MHz	I <sub>C</sub> = -20mA, V <sub>CE</sub> = -20V f = 20MHz
Output capacitance	C <sub>obo</sub>		12.9	20	pF	V <sub>CB</sub> = -20V, f = 1MHz <sup>(*)</sup>
Delay time	t <sub>d</sub>		95		ns	V <sub>CC</sub> = -100V.
Rise time	t <sub>r</sub>		73.8		ns	I <sub>C</sub> = -100mA,
Storage time	t <sub>s</sub>		1790		ns	I <sub>B1</sub> = 10mA, I <sub>B2</sub> = -20mA.
Fall time	t <sub>f</sub>		153.8		ns	

## Electrical characteristics (at $T_{amb}$ = 25°C unless otherwise stated)

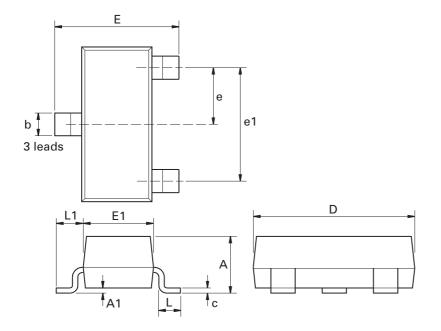
### NOTES:

(\*) Measured under pulsed conditions. Pulse width  ${\leq}300\mu s;$  duty cycle  ${\leq}2\%.$ 

## **Typical characteristics**



## Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
А	-	1.12	-	0.044	e1	1.90	NOM	0.075	NOM
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.120	0.003	0.008	L	0.25	0.62	0.018	0.024
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.0375	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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